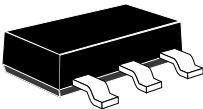


ZXM62N03G

30V N-CHANNEL ENHANCEMENT MODE MOSFET

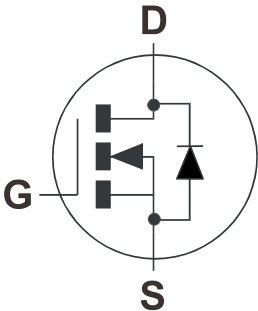
SUMMARY
 $V_{(BR)DSS} = 30V$; $R_{DS(on)} = 0.11\Omega$; $I_D = 4.7A$

DESCRIPTION
This new generation of High Density MOSFETs from Zetex utilises a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



SOT223

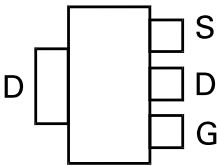
- FEATURES
- Low on-resistance
 - Fast switching speed
 - Low threshold
 - Low gate drive
 - SOT223 package



- APPLICATIONS
- DC-DC Converters
 - Audio Output Stage
 - Relay and Soleniod driving
 - Motor Control

ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXM62N03GTA	7"	12mm	1000 units
ZXM62N03GTC	13"	12mm	4000 units



Top View

- DEVICE MARKING
- ZXM6
2N03

ZXM62N03G

ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS}=10V$; $T_A=25^\circ C$)(b) ($V_{GS}=10V$; $T_A=70^\circ C$)(b) ($V_{GS}=10V$; $T_A=25^\circ C$)(a)	I_D	4.7 3.8 3.4	A
Pulsed Drain Current (c)	I_{DM}	16	A
Continuous Source Current (Body Diode) (b)	I_S	2.6	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	16	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	2.0 16	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	3.9 31	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J; T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	32	$^\circ C/W$

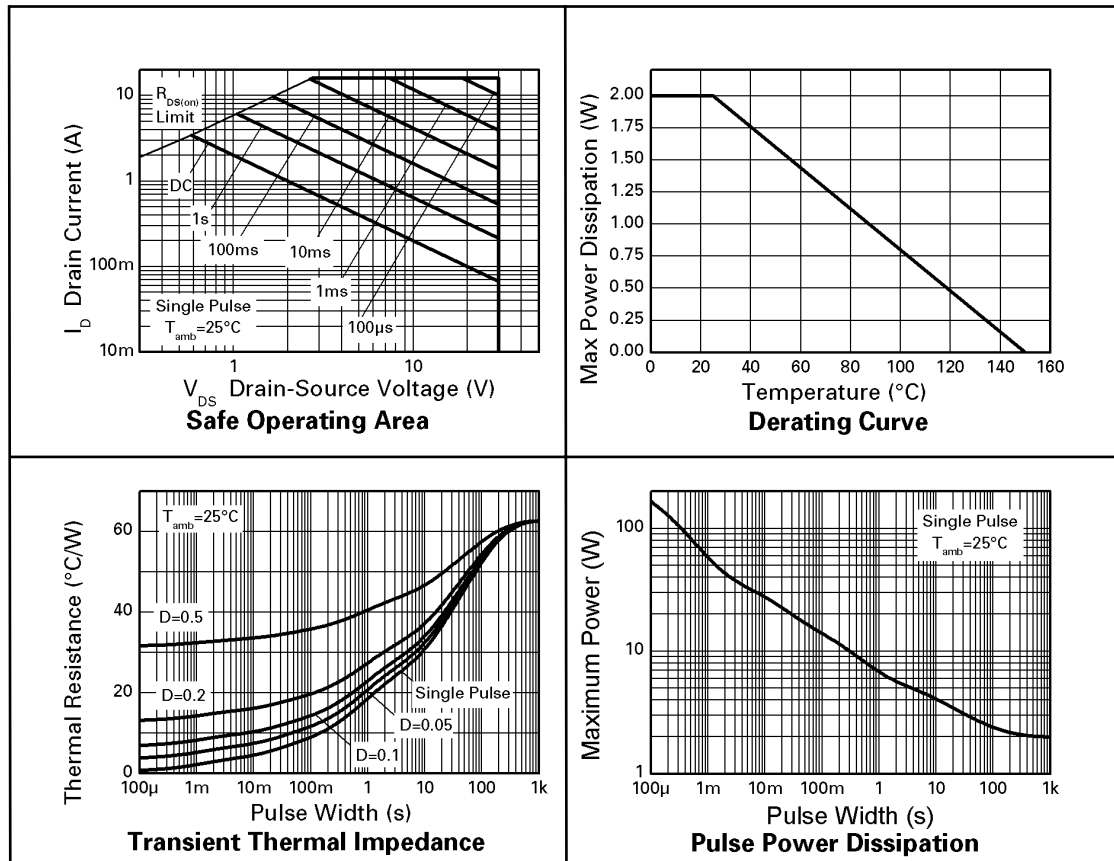
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width limited by maximum junction temperature.

ZXM62N03G



ZXM62N03G

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

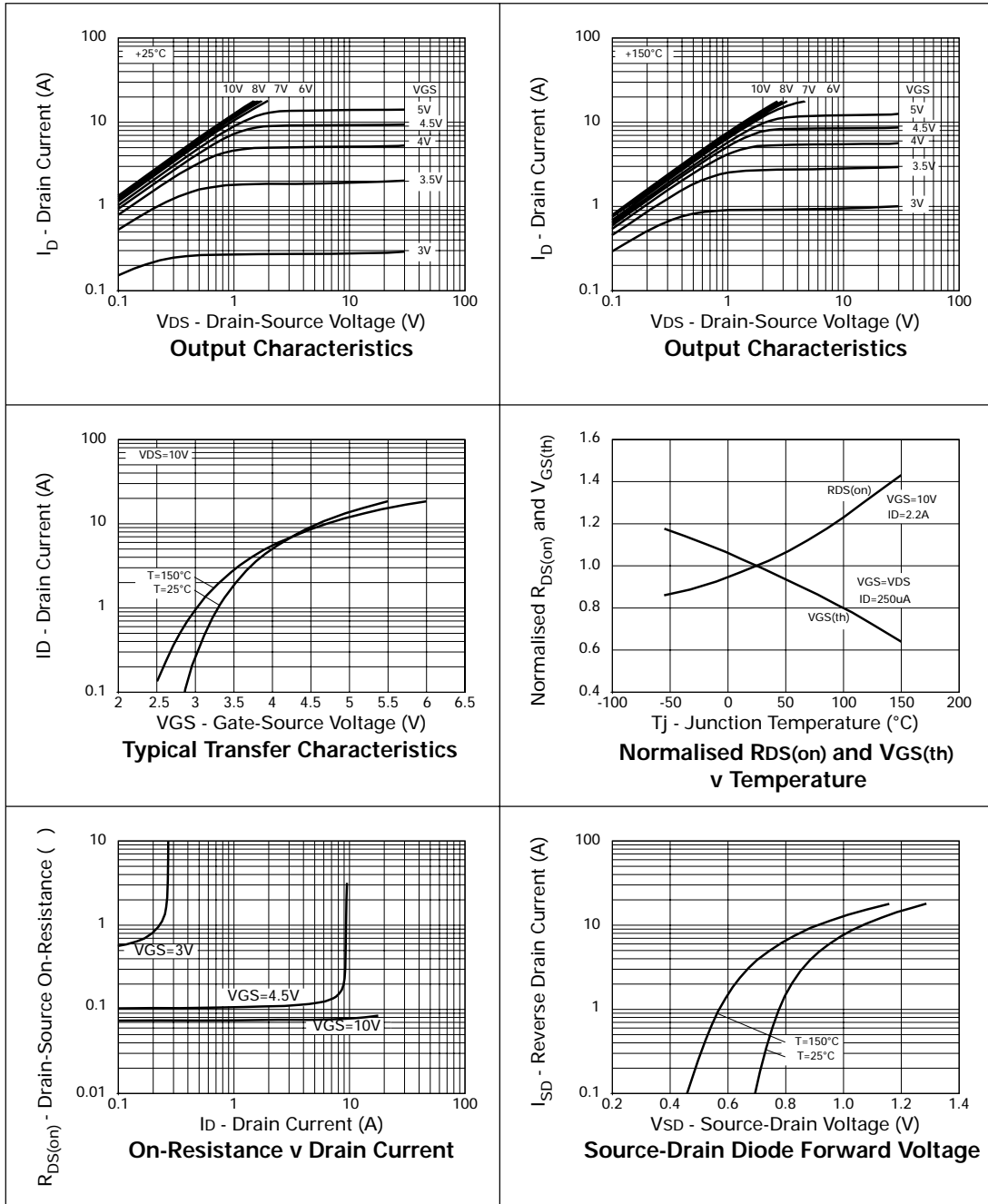
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1.0			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.11 0.15	Ω Ω	V _{GS} =10V, I _D =2.2A V _{GS} =4.5V, I _D =1.1A
Forward Transconductance (1)(3)	g _{fs}	1.1			S	V _{DS} =15V,I _D =1.1A
DYNAMIC (3)						
Input Capacitance	C _{iss}		380		pF	V _{DS} =25V, V _{GS} =0V, f=1MHZ
Output Capacitance	C _{oss}		90		pF	
Reverse Transfer Capacitance	C _{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		2.9		ns	V _{DD} =15V, I _D =2.2A R _G =6.0Ω, V _{GS} =10V
Rise Time	t _r		5.6		ns	
Turn-Off Delay Time	t _{d(off)}		11.7		ns	
Fall Time	t _f		6.4		ns	
Total Gate Charge	Q _g			9.6	nC	V _{DS} =24V,V _{GS} =10V, I _D =2.2A
Gate-Source Charge	Q _{gs}			1.7	nC	
Gate-Drain Charge	Q _{gd}			2.8	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}			0.95	V	T _J =25°C, I _S =2.2A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		18.8		ns	T _J =25°C, I _F =2.2A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		11.4		nC	

NOTES

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
(2) Switching characteristics are independent of operating junction temperature.
(3) For design aid only, not subject to production testing.

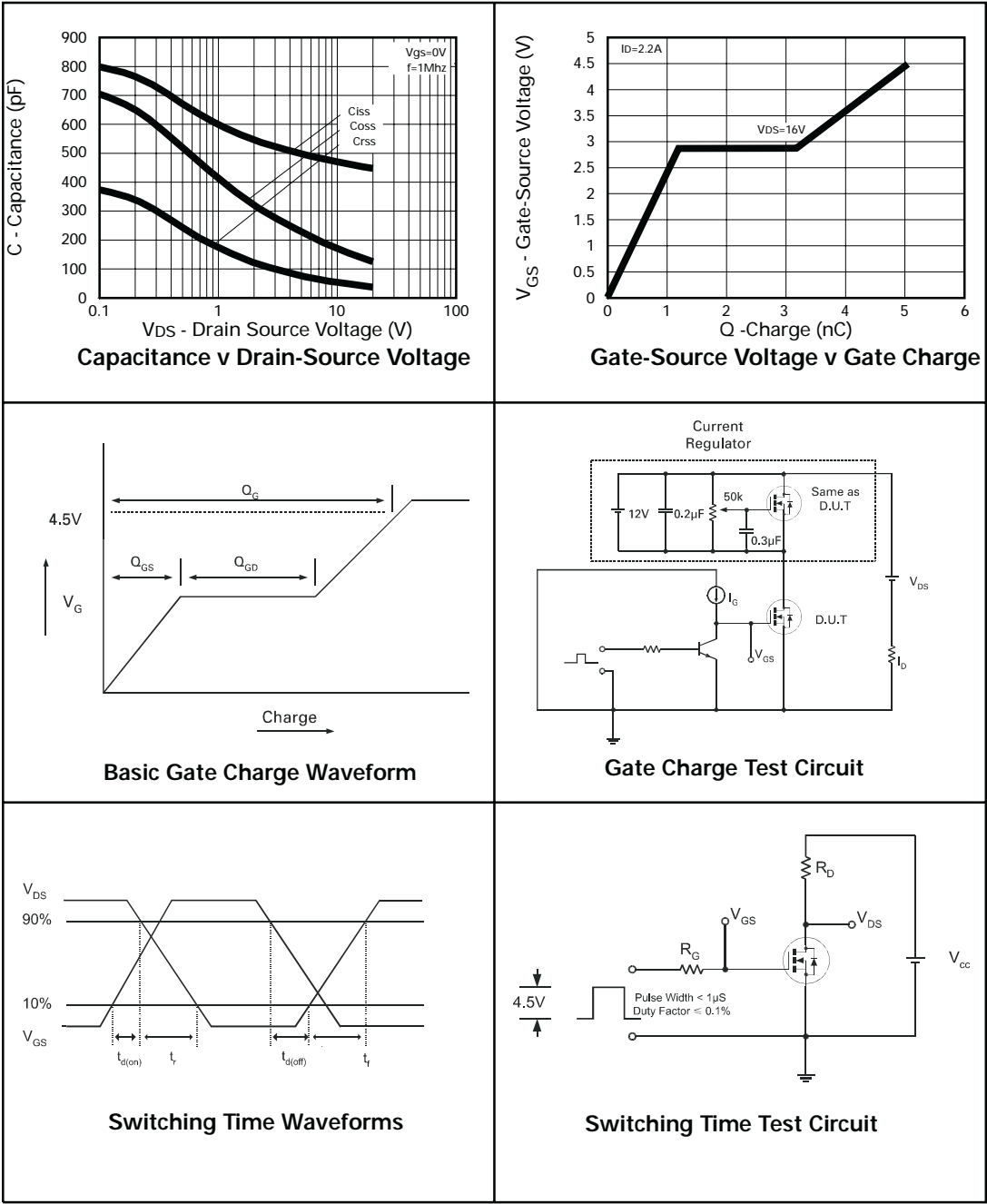
ZXM62N03G

TYPICAL CHARACTERISTICS



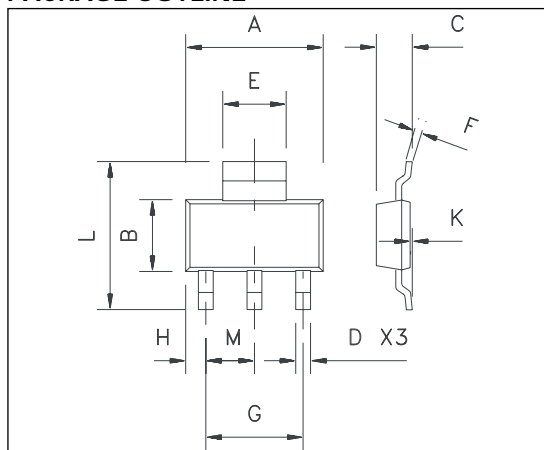
ZXM62N03G

TYPICAL CHARACTERISTICS



ZXM62N03G

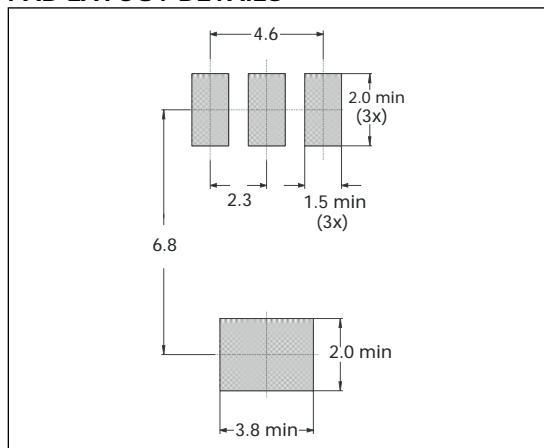
PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	6.3	6.7	0.248	0.264
B	3.3	3.7	0.130	0.146
C	-	1.7	-	0.067
D	0.6	0.8	0.024	0.031
E	2.9	3.1	0.114	0.122
F	0.24	0.32	0.009	0.13
G	NOM 4.6		NOM 0.181	
H	0.85	1.05	0.033	0.041
K	0.02	0.10	0.0008	0.004
L	6.7	7.3	0.264	0.287
M	NOM 2.3		NOM 0.0905	

PAD LAYOUT DETAILS



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